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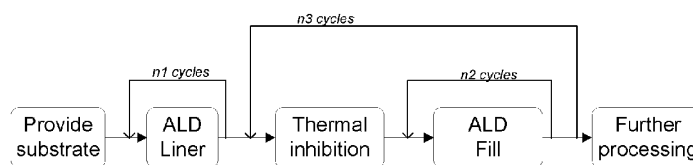


FIG. 3B

(57) Abstract: Inhibition of dielectric film growth is described. The inhibition may be used during atomic layer deposition (ALD) processes of dielectric material in gaps to facilitate bottom-up (or inside-out) gap fill. One or more inhibition operations are performed during gap fill. The inhibition operation modifies the surface of the gap in a manner that inhibits growth in subsequent ALD cycles.



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